TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

# 2SK2837

Chopper Regulator, DC-DC Converter and Motor Drive Applications

• Low drain-source ON resistance  $: RDS (ON) = 0.21 \Omega (typ.)$ 

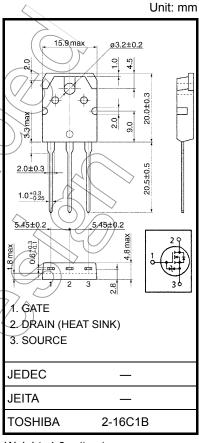
• High forward transfer admittance  $|Y_{fs}| = 17 \text{ S (typ.)}$ 

• Low leakage current  $: I_{DSS} = 100 \,\mu\text{A} \,(\text{max}) \,(V_{DSS} = 500 \,\text{V})$ 

• Enhancement-mode :  $V_{th} = 2.0 \sim 4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$ 

### **Absolute Maximum Ratings (Ta = 25°C)**

Characteri	stics	Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	500	V
Drain-gate voltage (R	<sub>GS</sub> = 20 kΩ)	$V_{DGR}$	500	A
Gate-source voltage	_	$V_{GSS}$	±30	> v
Drain current	DC (Note 1)	ΙD	20	Α
	Pulse (Note 1)	I <sub>DP</sub>	80	A
Drain power dissipatio	n (Tc = 25°C)	P <sub>D</sub>	150	/W
Single pulse avalanche	e energy (Note 2)	EAS	960	m2
Avalanche current		JAR .	20	Α
Repetitive avalanche energy (Note 3)		(EAR	15	mJ
Channel temperature		Tch	150	~c
Storage temperature r	ange	// \hatatat	-55~150	√)°C



Weight: 4.6 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	Rth (ch-c)	0.833	°C/W
Thermal resistance, channel to ambient	Rth (ch-a)	50	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 4.08 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 20 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.

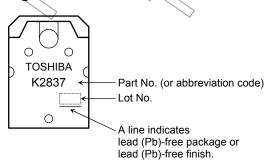
## **Electrical Characteristics (Ta = 25°C)**

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	$I_{GSS}$	V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0 V	_	_	±10	μΑ
Gate-source bro	eakdown voltage	V (BR) GSS	I <sub>G</sub> = ±10 μA, V <sub>DS</sub> = 0 V	±30	_	_	V
Drain cut-off cu	rrent	I <sub>DSS</sub>	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V		_	100	μΑ
Drain-source br voltage	reakdown	V <sub>(BR)</sub> DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	500	1/2	ı	٧
Gate threshold	voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.0	) —	4.0	٧
Drain-source O	N resistance	R <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	<u> </u>	0.21	0.27	Ω
Forward transfe	r admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 10 A		17		S
Input capacitano	ce	C <sub>iss</sub>		· —	3720	-	
Reverse transfe	r capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	340	-	pF
Output capacita	nce	C <sub>oss</sub>	4(>>	_	165	4	
Switching time	Rise time	t <sub>r</sub>	V <sub>GS</sub> 10V ID=10A V <sub>GS</sub> 0V IV		30	> —	
	Turn-on time	t <sub>on</sub>	$R_{L}=20\Omega$		70	) _	20
	Fall time	t <sub>f</sub>	Van = 200V	$\bigcirc$	50	_	ns
	Turn-off time	t <sub>off</sub>	$V_{DD} = 200V$ $Duty \leq 1\%, t_{W} = 10\mu s$	) _	290		
Total gate charg plus gate-drain		Qg		ı	80	ı	
Gate-source ch	arge	Q <sub>gs</sub>	$V_{DD} = 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 6 \text{ A}$	_	48	_	nC
Gate-drain ("mi	ller") Charge	Qgd			32	_	

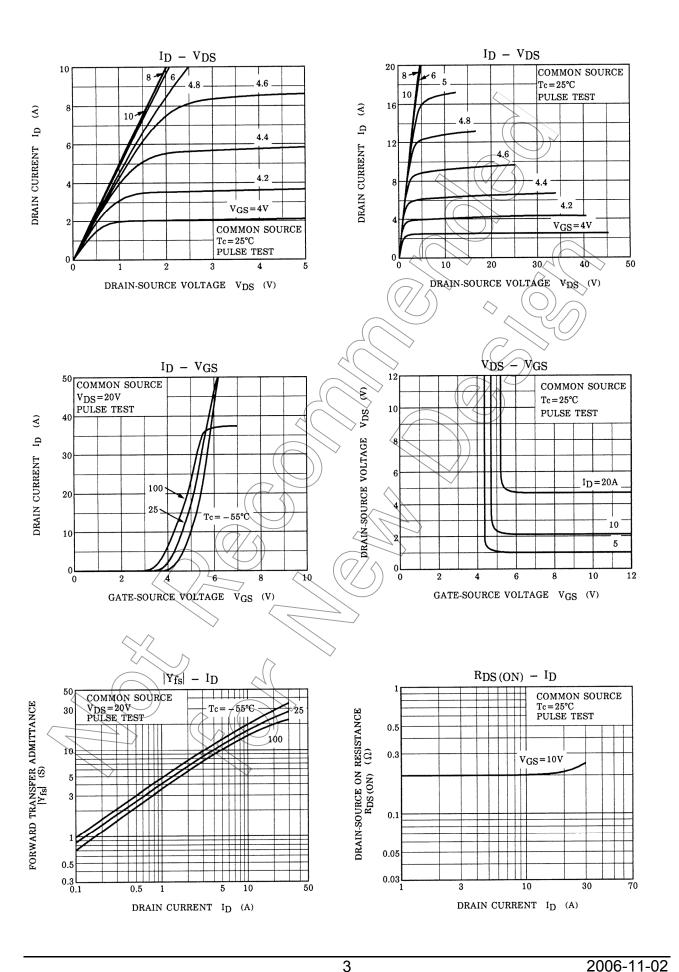
# Source-Drain Ratings and Characteristics (Ta = 25°C)

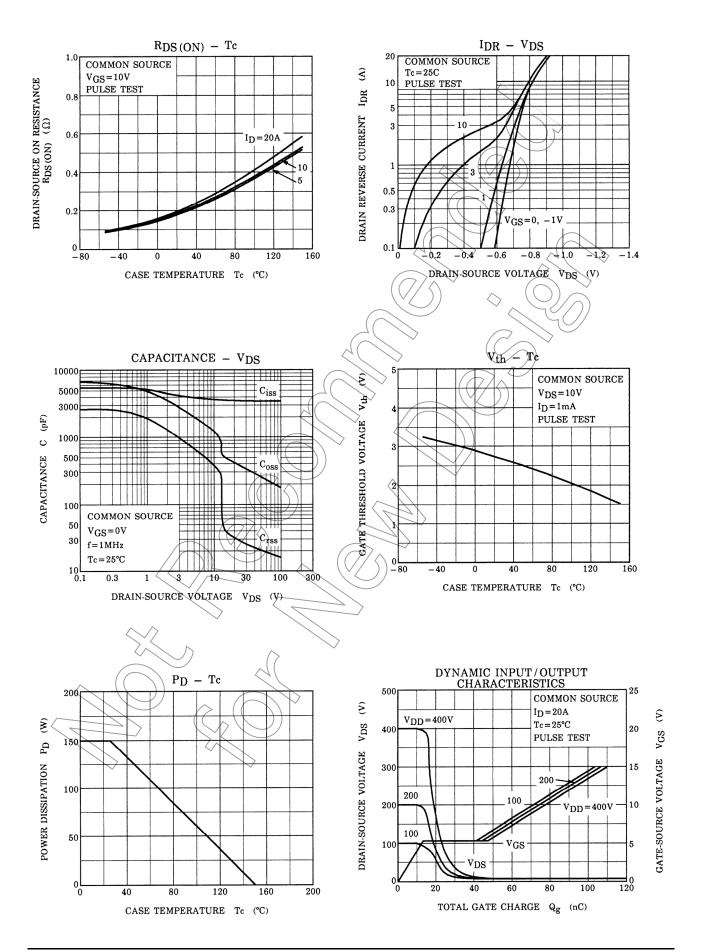
Characteristics Symbo	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	-	_	_	20	А
Pulse drain reverse current (Note 1)	_	_	_	80	Α
Forward voltage (diode) V <sub>DSF</sub>	I <sub>DR</sub> = 20 Å, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time t <sub>rr</sub>	I <sub>DR</sub> = 20 A, V <sub>GS</sub> = 0 V	_	540	_	ns
Reverse recovery charge Qrr	dl <sub>DR</sub> / dt = 100 A / μs	_	5.4	_	μC

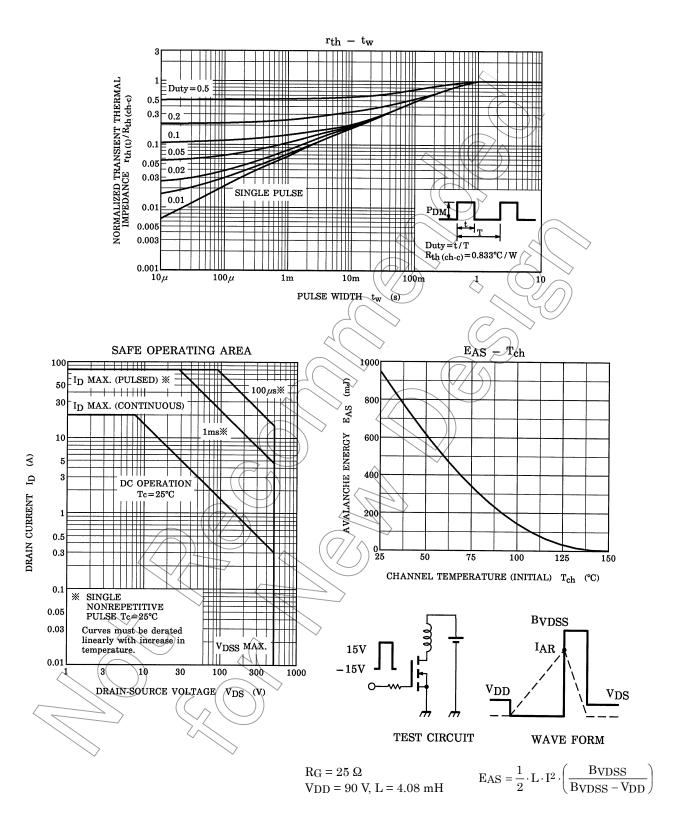
## Marking

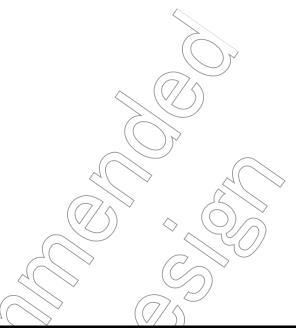


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